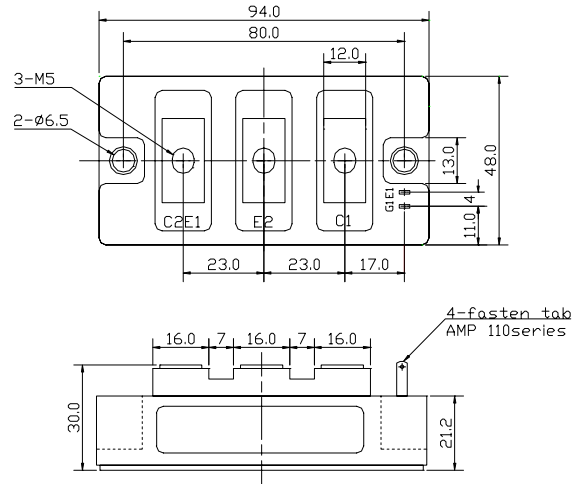
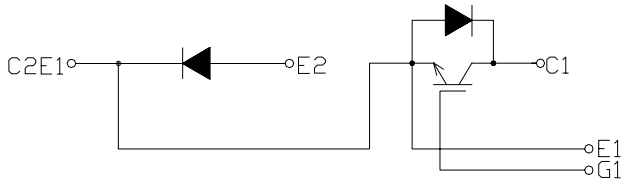


回路図 : CIRCUIT
外形寸法図 : OUTLINE DRAWING


Dimension: [mm]

最大定格 : MAXIMUM RATINGS (T_c = 25)

重量 : 320 g

Item	Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CES}	6 0 0	V
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GES}	± 2 0	V
コレクタ電流 Collector Current	DC	I _c 2 0 0	A
	1 m s	I _{CP} 4 0 0	
コレクタ損失 Collector Power Dissipation	P _c	7 8 0	W
接合温度 Junction Temperature Range	T _j	- 4 0 ~ + 1 5 0	
保存温度 Storage Temperature Range	T _{stg}	- 4 0 ~ + 1 2 5	
絶縁耐圧 (Terminal to Base AC, 1minute) Isolation Voltage	V _{iso}	2, 5 0 0	V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink	3 (3 0 . 6)	N · m (kgf · cm)
	Busbar to Main Terminal	2 (2 0 . 4)	

電気的特性 : ELECTRICAL CHARACTERISTICS (T_c = 25)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I _{CES}	V _{CE} = 600V, V _{GE} = 0V	-	-	2.0	mA	
ゲート漏れ電流 Gate-Emitter Leakage Current	I _{GES}	V _{GE} = ±20V, V _{CE} = 0V	-	-	1.0	μA	
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 200A, V _{GE} = 15V	-	2.1	2.6	V	
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _c = 200mA	4.0	-	8.0	V	
入力容量 Input Capacitance	C _{ies}	V _{CES} = 10V, V _{GE} = 0V, f = 1MHz	-	20,000	-	pF	
スイッチング時間 Switching Time	上昇時間 Rise Time	t _r	V _{CC} = 300V R _L = 3Ω R _G = 3.6Ω V _{GE} = ±15V	-	0.15	0.30	μs
	ターンオン時間 Turn-on Time	t _{on}		-	0.25	0.40	
	下降時間 Fall Time	t _f		-	0.20	0.35	
	ターンオフ時間 Turn-off Time	t _{off}		-	0.45	0.70	

フリーホイールダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS (T_c = 25)

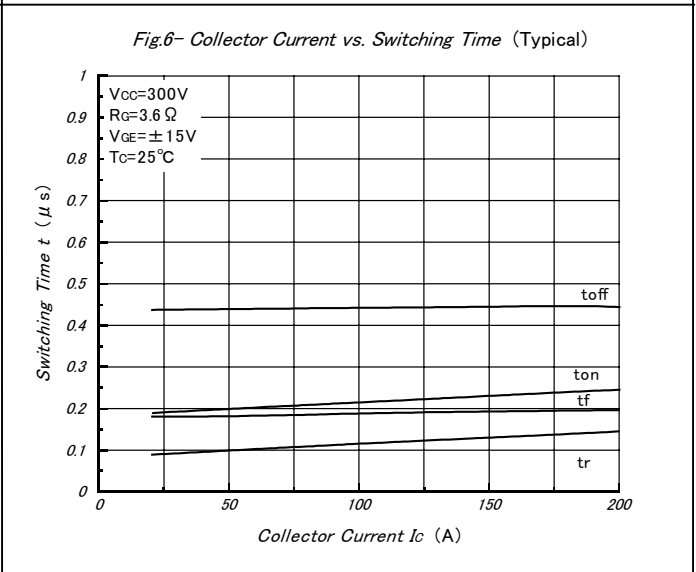
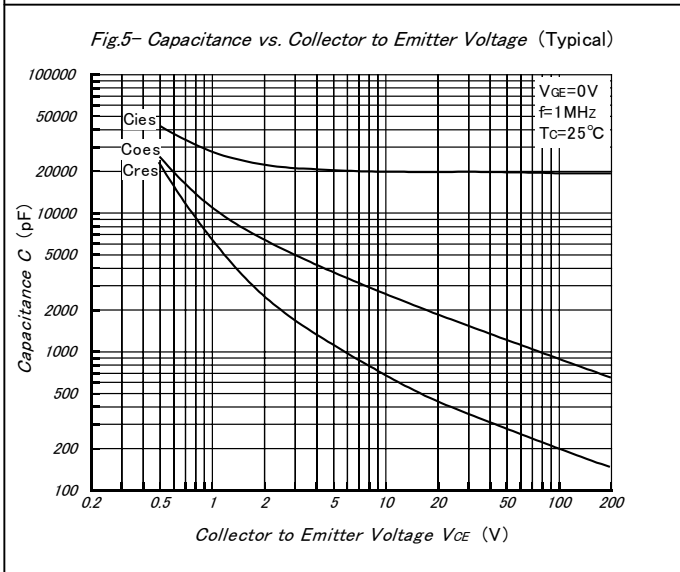
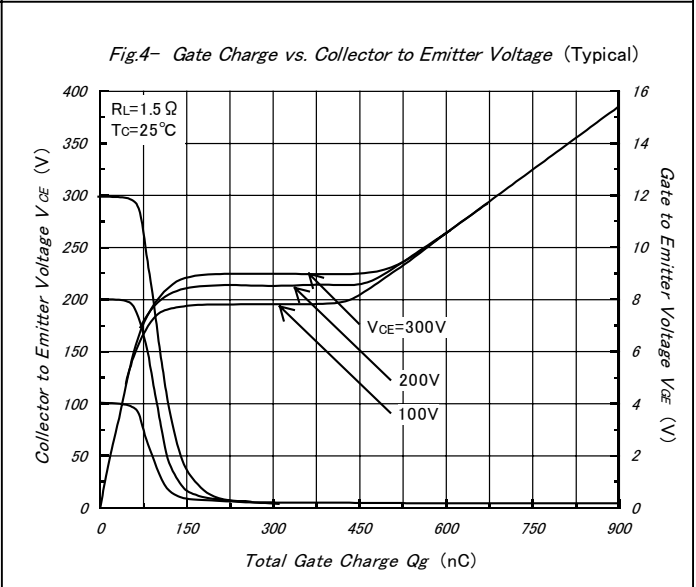
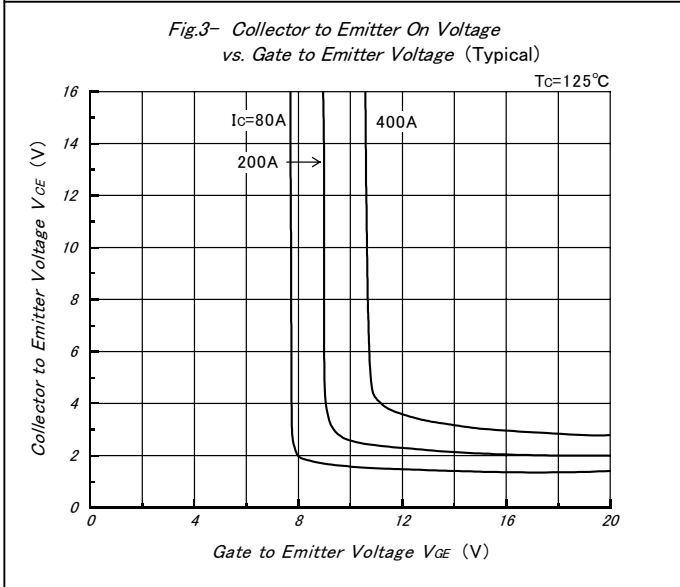
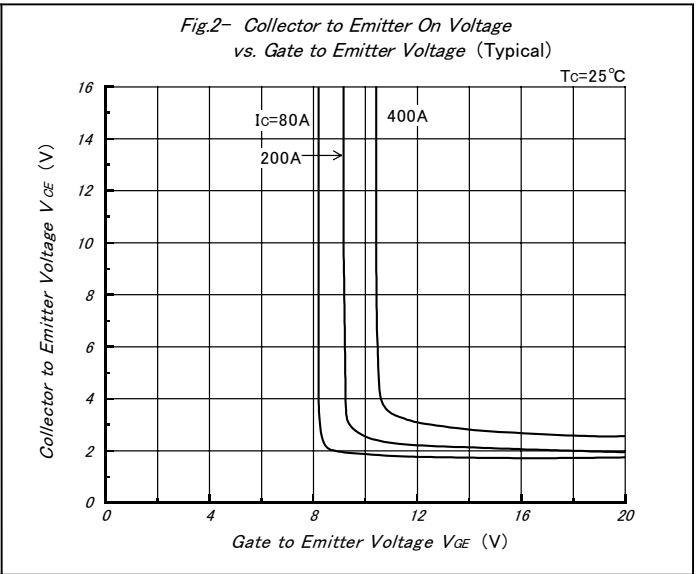
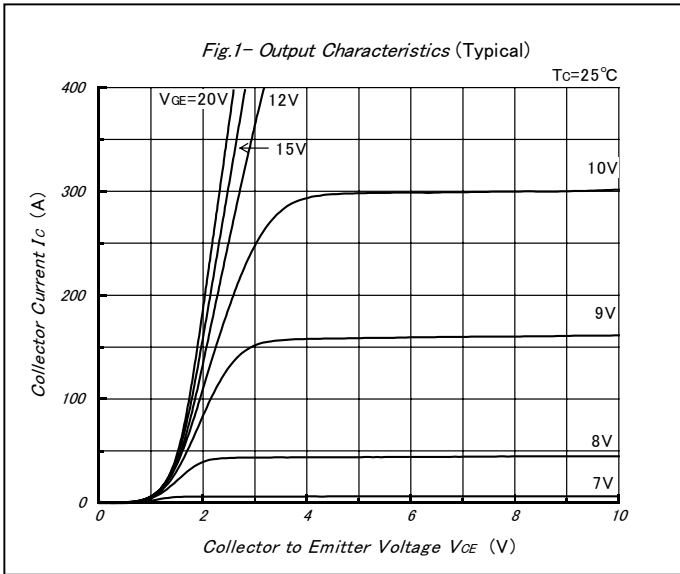
Item	Symbol	Rated Value	Unit
順電流 Forward Current	DC	I _F 2 0 0	A
	1 m s	I _{FM} 4 0 0	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V _F	I _F = 200A, V _{GE} = 0V	-	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t _{rr}	I _F = 200A, V _{GE} = -10V di/dt = 200A/μs	-	0.15	0.25	μs

熱的特性 : THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	I G B T	Junction to Case	-	-	0.16	/ W
	Diode		-	-	0.38	

PCHMB200A6A



PCHMB200A6A

Fig.7- Series Gate Impedance vs. Switching Time (Typical)

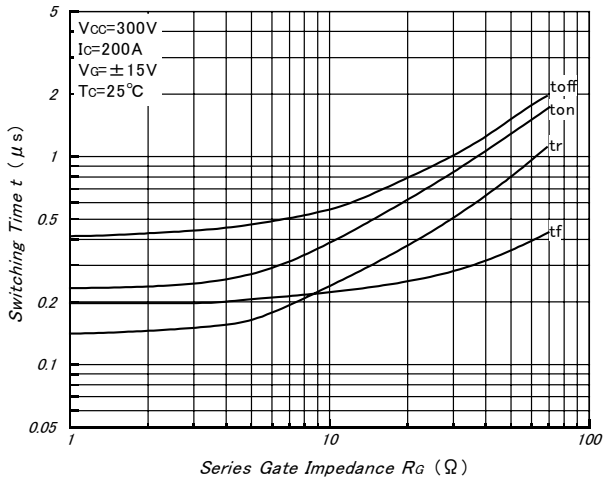


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

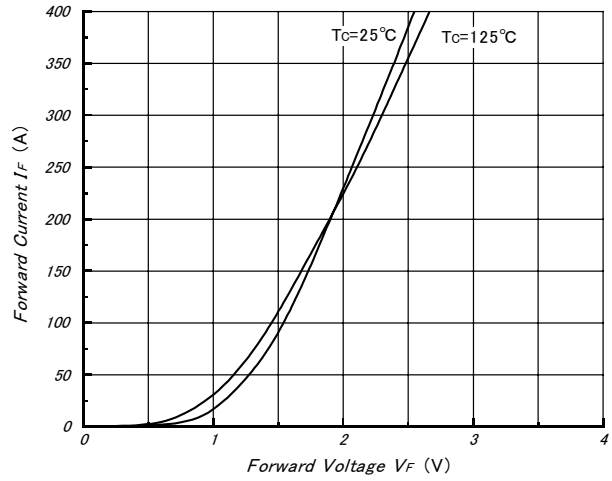


Fig.9- Reverse Recovery Characteristics (Typical)

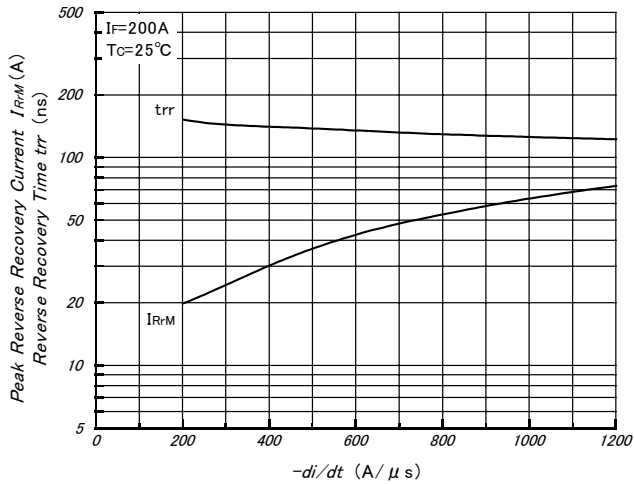


Fig.10- Reverse Bias Safe Operating Area (Typical)

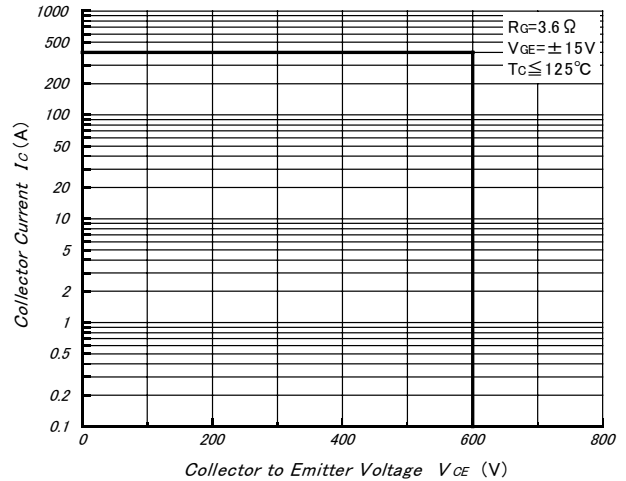


Fig.11- Transient Thermal Impedance

